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(SE). HUHTAOJA, Tommy [SE/SE]; Rullstensgränd 6,
S-135 50 Tyresö (SE).

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(74) Agent: DR LUDWIG BRANN PATENTBYRÅ AB; P O
Box 1344, S-751 43 Uppsala (SE).

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(71) Applicant (for all designated States except US): SILEX
MICROSYSTEMS AB [SE/SE]; Electrum 222, S-164 40
Kista (SE).

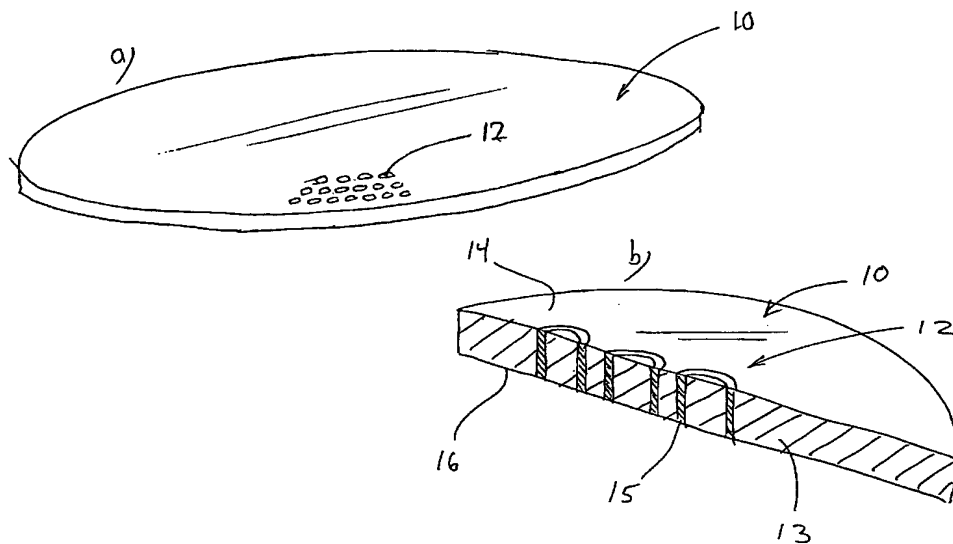
(72) Inventors; and

(75) Inventors/Applicants (for US only): KÄLVESTEN,
Edvard [SE/SE]; Edelcrantzvägen 20, S-129 38 Hägersten
(SE). EBEFORS, Thorbjörn [SE/SE]; Kalkkärrsvägen
28, S-141 41 Huddinge (SE). SVEDIN, Niklas [SE/SE];
Karlavägen 27, S-114 31 Stockholm (SE). RANGSTEN,
Pelle [SE/SE]; Vretalundsvägen 8, S-743 34 Storvreta

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(54) Title: ELECTRICAL CONNECTIONS IN SUBSTRATES



(57) Abstract: The invention relates to a method of making an electrical connection between a first (top) and a second (bottom) surface of a conducting or semi-conducting substrate. It comprising creating a trench in the first surface, and establishing an insulating enclosure entirely separating a portion of said substrate, defined by said trench. It also relates to a product usable as a starting substrate for the manufacture of micro-electronic and/or micro-mechanic devices, comprising a flat substrate of a semi-conducting or conducting material, and having a first and a second surface and at least one electrically conducting member extending through said substrate. The electrically conducting member is insulated from surrounding material of the flat substrate by a finite layer of an insulating material, and comprises the same material as the substrate, i.e. it is made from the wafer material.

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